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Authors: Jianbo Dai, Honghua Su, Tengfei Yu, Hao Hu, Wenbo Zhou, Wenfeng Ding



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## Experimental investigation on the material removal mechanism in during grinding silicon carbide ceramics with single diamond grain

Jianbo Dai<sup>1,2</sup>, Honghua Su<sup>1,\*</sup>, Tengfei Yu<sup>1</sup>, Hao Hu<sup>1</sup>, Wenbo Zhou<sup>1</sup>, Wenfeng Ding<sup>1</sup>

<sup>1</sup>College of Mechanical and Electrical Engineering, Nanjing University of Aeronautics and Astronautics, Nanjing 210016, P.R. China

<sup>2</sup>Department of Mechanical Engineering, University of Michigan, Ann Arbor MI, USA

\*Corresponding author. Tel./fax: 86-25-84892901

E-mail: shh@nuaa.edu.cn (H.H. Su)

### Highlights

- The single diamond grain grinding test was firstly proposed to decouple the effect of grinding speed and UCT on the SiC material removal mechanism during elevating the grinding wheel speed.
- The critical grinding wheel speed  $v_s=100, 80, 80$  m/s was determined at the  $a_{gmax}= 0.03, 0.3, 1\mu\text{m}$  respectively based on the effect of grinding wheel speed on the grinding force and subsurface morphology.
- The results demonstrated three grinding regimes: ductile, ductile-brittle, and brittle. Critical M-UCT values, such as  $0.3, 1\mu\text{m}$ , were determined based on the surface and subsurface morphology, grinding forces, grinding energy to quantify the material removal modes.

**Abstract** A single grain grinding experiment with fixed speed ratio  $v_s/v_w$  was designed to decouple the effect of grinding speed and undeformed chip thickness (UCT) on the SiC material removal mechanism during elevating the grinding wheel speed. Ground surface and subsurface topography, grinding forces, and specific energy were measured with grinding speed ranging from 20 to 160 m/s and maximum UCT  $a_{gmax}$  from 0.02 to 3  $\mu\text{m}$ . The results demonstrated the grinding force and specific grinding energy show an evident decreased tendency with the increasing of grinding speed, despite the  $a_{gmax}$  value was kept at 0.03, 1  $\mu\text{m}$ . However, at  $a_{gmax}=0.3\mu\text{m}$ , the grinding force has a peak value with the increment of grinding wheel speed. The subsurface has the same trend. Based on the subsurface morphologies, grinding forces, grinding energy, the critical grinding wheel speeds  $v_s=100, 80, 80$  m/s were determined at the  $a_{gmax}= 0.03, 0.3, 1\mu\text{m}$ ,

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